Power Transistor (-100V, -2A) 2SB1580 / 2SB1316

Features

- 1) Darlington connection for high DC current gain.
- 2) Built-in resistor between base and emitter.
- 3) Built-in damper diode.
- 4) Complements the 2SD2195 / 2SD1980.

● Absolute maximum ratings (Ta = 25°C)

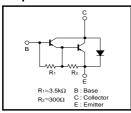
F	Parameter	Symbol	Limits	Unit		
Collector-base voltage		Vсво	-100	V		
Collector-emitter voltage		Vceo	-100	V		
Emitter-base voltage		Vebo	-8	V		
Collector current		Ic	-2	A(DC)		
		IC IC	-3	A(Pulse)	*1	
Collector power dissipation	2SB1580		2	w	*2	
	2SB1316	Pc	1	VV	~2	
			10	W(Tc=25°C)		
Junction temperature		Tj	150	°C		
Storage temperature		Tstg	-55~+150	°C		

^{*1} Single pulse Pw=100ms *2 When mounted on a 40 x 40 x 0.7 mm ceramic board

Packaging specifications and hre

Туре	2SB1580	2SB1316	
Package	MPT3	CPT3	
hre	1k~10k	1k~10k	
Marking	BN∗	-	
Code	T100	TL	
Basic ordering unit (pieces)	1000	2500	

● Equivalent circuit



● Electrical characteristics (Ta = 25°C)

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Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Collector-base breakdown voltage	ВУсво	-100	-	-	V	Ic = -50μA	
Collector-emitter breakdown voltage	BVceo	-100	-	-	V	Ic=-5mA	
Collector cutoff current	Ісво	-	-	-10	μΑ	Vcb = -100V	
Emitter cutoff current	Iево	-	-	-3	mA	V _{EB} = -7V	
Collector-emitter saturation voltage	VCE(sat)	-	-	-1.5	V	Ic/I _B =-1A/-1mA	*
DC current transfer ratio	hfe	1000	-	10000	-	Vce = -2V , Ic = -1A	*
Output capacitance	Cob	_	35	_	pF	Vcs = -10V , IE = 0A , f = 1MHz	

• External dimensions (Units : mm)

